

Kwong-Kau Tiong

List of Publications by Year in descending order

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papers

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#	ARTICLE	IF	CITATIONS
1	The Study of Optical Properties of III ₂ V ₃ Defect Semiconductor Group Compounds Ga ₂ S ₃ , Ga ₂ Se ₃ , In ₂ S ₃ , and In ₂ Se ₃ . Advanced Photonics Research, 2021, 2, 2000110.	3.6	8
2	Wind Technologies for Wake Effect Performance in Windfarm Layout Based on Population-Based Optimization Algorithm. Energies, 2021, 14, 4125.	3.1	2
3	Anisotropic effects in the Raman scattering of Re-doped 2H-MoSe ₂ layered semiconductors. Results in Physics, 2017, 7, 4096-4100.	4.1	19
4	A Compact Experimental Planar Antenna with a USB Connector for Mobile Phone Application. International Journal of Antennas and Propagation, 2015, 2015, 1-6.	1.2	0
5	Investigation of off-board DPI method. , 2015, , .		2
6	Incident-angle-dependent reflectance in distributed Bragg reflectors fabricated from ZnO/MgO multilayer films. Optical Review, 2014, 21, 651-654.	2.0	7
7	The study of temperature dependent strain in Ge epilayer with SiGe/Ge buffer layer on Si substrate with different thickness. Applied Physics Letters, 2014, 104, 241605.	3.3	5
8	Characterization and enhanced field emission properties of carbon nanotube bundle arrays coated with N-doped nanocrystalline anatase TiO ₂ . Materials Chemistry and Physics, 2014, 143, 1378-1383.	4.0	7
9	Characterization of Ge/Si _{0.16} Ge _{0.84} multiple quantum wells on Ge-on-Si virtual substrate using piezoreflectance spectroscopy. Solid State Communications, 2013, 167, 5-9.	1.9	1
10	Photoreflectance Spectroscopy Characterization of Ge/Si _{0.16} Ge _{0.84} Multiple Quantum Wells on Ge Virtual Substrate. Advances in Condensed Matter Physics, 2013, 2013, 1-6.	1.1	2
11	Anomalous structural phase transition properties in ReSe ₂ and Au-doped ReSe ₂ . Journal of Chemical Physics, 2012, 137, 024509.	3.0	14
12	Structural and Band-Edge Properties of Cu(Al _x In _{1-x})S ₂ (0 ≤ x ≤ 1) Series Chalcopyrite Semiconductors. Solid State Phenomena, 2012, 194, 133-138.	0.3	3
13	A Novel On-Glass Antenna for Mobile Handset Applications. , 2012, , .		9
14	A Novel On-Glass GPS Antenna for Handset Applications. Procedia Engineering, 2012, 29, 3376-3380.	1.2	1
15	Raman scattering characterization of Zn _{1-x} Mg _y Be _x Se mixed crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1752-1755.	0.8	0
16	Optical characterization of Zn _{0.35} Cd _{0.44} Mg _{0.21} Se crystalline alloy by polarization-dependent contactless electroreflectance measurements. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1756-1759.	0.8	0
17	Above-room-temperature photoluminescence from a strain-compensated Ge/Si _{0.15} Ge _{0.85} multiple-quantum-well structure. Applied Physics Letters, 2012, 100, .	3.3	18
18	Optical characterization of a strain-compensated GaAs _{0.64} Sb _{0.36} /GaAs _{0.79} P _{0.21} quantum well structure grown by metal organic vapor phase epitaxy. Materials Chemistry and Physics, 2012, 134, 797-802.	4.0	3

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19	Deposition and characterization of IrO _x nanofoils on carbon nanotube templates by reactive magnetron sputtering. <i>Thin Solid Films</i> , 2012, 520, 2409-2413.	1.8	16
20	Influence of anionic substitution on the electrolyte electroreflectance study of band edge transitions in single crystal Cu ₂ ZnSn(SxSe _{1-x}) ₄ solid solutions. <i>Optical Materials</i> , 2012, 34, 1362-1365.	3.6	57
21	Characterization of freestanding semi-insulating Fe-doped GaN by photoluminescence and electromodulation spectroscopy. <i>Journal of Applied Physics</i> , 2011, 109, 123508.	2.5	17
22	Piezoreflectance and Raman Characterization of Mo _{1-x} W _x S ₂ Layered Mixed Crystals. <i>Solid State Phenomena</i> , 2011, 170, 55-59.	0.3	8
23	Temperature-dependent photoluminescence and contactless electroreflectance characterization of a Zn _x Cd _{1-x} Se/Zn _x Cd _{1-x} Se/Mg _{1-x} Zn _x Se asymmetric coupled quantum well structure. <i>Journal of Alloys and Compounds</i> , 2011, 509, 3751-3755.		1
24	Absorption-edge anisotropy of Cu ₂ ZnSiQ ₄ (Q = S, Se) quaternary compound semiconductors. <i>Journal of Alloys and Compounds</i> , 2011, 509, 4924-4928.	5.5	23
25	Polarization-dependent electrolyte electroreflectance study of Cu ₂ ZnSiS ₄ and Cu ₂ ZnSiSe ₄ single crystals. <i>Journal of Alloys and Compounds</i> , 2011, 509, 7105-7108.	5.5	44
26	Anisotropy of the spectroscopy properties of the wurtz-stannite Cu ₂ ZnGeS ₄ single crystals. <i>Optical Materials</i> , 2011, 34, 183-188.	3.6	39
27	Characterization of IrO ₂ /CNT nanocomposites. <i>Journal of Materials Science: Materials in Electronics</i> , 2011, 22, 890-894.	2.2	14
28	Deposition and Characterization of IrO ₂ Nanocrystals on Vertically Aligned Carbon Nanotubes by MOCVD. <i>Solid State Phenomena</i> , 2011, 170, 70-73.	0.3	0
29	A nanostructured electrode of IrO _x foil on the carbon nanotubes for supercapacitors. <i>Nanotechnology</i> , 2011, 22, 355708.	2.6	22
30	Optical Characterization of Electronic Structure of CuInS ₂ and CuAlS ₂ Chalcopyrite Crystals. <i>Solid State Phenomena</i> , 2011, 170, 21-24.	0.3	1
31	Optical study of GaAs _{1-x} Sb _x layers grown on GaAs substrates by gas-source molecular beam epitaxy. <i>Materials Chemistry and Physics</i> , 2010, 124, 558-562.	4.0	7
32	Photoluminescence and surface photovoltage spectroscopy characterization of highly strained InGaAs/GaAs quantum well structures grown by metal organic vapor phase epitaxy. <i>Materials Chemistry and Physics</i> , 2010, 124, 1126-1133.	4.0	9
33	Growth and characterization of well-aligned densely-packed rutile TiO ₂ nanocrystals on sapphire (100) and (012) substrates by reactive magnetron sputtering. <i>Thin Solid Films</i> , 2010, 518, 4121-4125.	1.8	12
34	Characterization of Zn _{0.95} Be _x Mn _{0.05} Se mixed crystals by photoluminescence and contactless electroreflectance. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1460-1462.	0.8	0
35	Photoluminescence and photoreflectance characterization of Zn _x Cd _{1-x} Se/MgSe multiple quantum wells. <i>Journal of Applied Physics</i> , 2010, 108, 123105.	2.5	4
36	Contactless electroreflectance and photoluminescence characterization of Zn _{0.68} Be _{0.06} Mg _{0.26} Se crystalline alloys. <i>Journal of Alloys and Compounds</i> , 2010, 491, 472-476.	5.5	4

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37	Temperature-dependent study of the band-edge excitonic transitions of Cu ₂ ZnSiS ₄ single crystals by polarization-dependent piezoreflectance. Journal of Alloys and Compounds, 2010, 506, 46-50.	5.5	15
38	Raman study of 2H-Mo _{1-x} W _x S ₂ layered mixed crystals. Journal of Alloys and Compounds, 2010, 506, 940-943.	5.5	81
39	Enhanced field emission properties of IrO ₂ coated carbon nanotube bundle arrays. , 2010, , .		0
40	Optical studies of type-I GaAs _{1-x} Sb _x /GaAs multiple quantum well structures. Journal of Applied Physics, 2009, 105, 123523.	2.5	10
41	(301) and (101) RuO ₂ twins on nanostructural rutile TiO ₂ template. Materials Chemistry and Physics, 2009, 117, 544-549.	4.0	4
42	Structural and luminescent property of gallium chalcogenides GaSe _{1-x} S _x layer compounds. Journal of Materials Science: Materials in Electronics, 2009, 20, 207-210.	2.2	9
43	Raman spectroscopy study of the phase transformation on nanocrystalline titania films prepared via metal organic vapour deposition. Journal of Materials Science: Materials in Electronics, 2009, 20, 303-306.	2.2	33
44	Growth and characterization of well-aligned rutile TiO ₂ nanocrystals on sapphire substrates via metal organic vapour deposition. Journal of Materials Science: Materials in Electronics, 2009, 20, 332-335.	2.2	5
45	In-plane anisotropic electrical and optical properties of gold-doped rhenium disulphide. Journal of Materials Science: Materials in Electronics, 2009, 20, 476-479.	2.2	7
46	Rapid thermal annealing effects on the structural and optical properties of ZnO films deposited on Si substrates. Journal of Luminescence, 2009, 129, 148-152.	3.1	95
47	Synthesis and structural characterization of twinned V-shaped IrO ₂ nanowedges on TiO ₂ nanorods via MOCVD. Journal of Alloys and Compounds, 2009, 480, 107-110.	5.5	7
48	Optical anisotropy of Au-doped ReS ₂ crystals. Journal of Alloys and Compounds, 2009, 480, 94-96.	5.5	16
49	Synthesis and characterization of needle-like IrSe ₂ microrods. Journal of Alloys and Compounds, 2009, 480, 70-72.	5.5	2
50	Optical anisotropy of near band-edge transitions in zinc oxide nanostructures. Journal of Alloys and Compounds, 2009, 480, 50-53.	5.5	5
51	Growth and structural characterization of well-aligned RuO ₂ nanorods on LiNbO ₃ (100) via MOCVD. Journal of Alloys and Compounds, 2009, 480, 100-103.	5.5	0
52	Synthesis of IrO ₂ nanocrystals on carbon nanotube bundle arrays and their field emission characteristics. Journal of Alloys and Compounds, 2009, 487, 659-664.	5.5	18
53	Design of a Multiband Antenna for Mobile Handset Operations. IEEE Antennas and Wireless Propagation Letters, 2009, 8, 200-203.	4.0	83
54	Synthesis and characterization of well-aligned anatase TiO ₂ nanocrystals on fused silica via metal-organic vapor deposition. CrystEngComm, 2009, 11, 2313.	2.6	18

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73	Design of dual wideband WLAN antenna. , 2007, , .		0
74	Optical characterization of a Cd _{0.85} Mg _{0.15} Se mixed crystal. Journal of Physics Condensed Matter, 2007, 19, 266002.	1.8	3
75	Raman scattering characterization of well-aligned RuO ₂ and IrO ₂ nanocrystals. Journal of Raman Spectroscopy, 2007, 38, 737-749.	2.5	112
76	Improved optical and structural properties of ZnO thin films by rapid thermal annealing. Solid State Communications, 2007, 143, 250-254.	1.9	63
77	Growth and characterization of molybdenum-doped rhenium diselenide. Materials Chemistry and Physics, 2007, 104, 105-108.	4.0	5
78	Effect of length, spacing and morphology of vertically aligned RuO ₂ nanostructures on field-emission properties. Nanotechnology, 2006, 17, 3149-3153.	2.6	19
79	Growth and Characterization of Well-Aligned RuO ₂ Nanocrystals on Oxide Substrates via Reactive Sputtering. Crystal Growth and Design, 2006, 6, 2501-2506.	3.0	22
80	Characterization of near band-edge properties of synthetic p-FeS ₂ iron pyrite from electrical and photoconductivity measurements. Journal of Alloys and Compounds, 2006, 422, 321-327.	5.5	13
81	Temperature dependence of the band edge excitonic transitions of a wurtzite-type Cd _{0.925} Be _{0.075} Se mixed crystal. Solid State Communications, 2006, 137, 82-86.	1.9	4
82	Raman scattering characterization of vertical aligned 1D IrO ₂ nanocrystals grown on single crystal oxide substrates. Solid State Communications, 2006, 137, 310-314.	1.9	14
83	Temperature dependence of absorption edge anisotropy in 2H- MoSe ₂ layered semiconductors. Solid State Communications, 2006, 139, 176-180.	1.9	20
84	Growth and characterization of vertically aligned IrO ₂ one dimensional nanocrystals on LiNbO ₃ (100) via reactive sputtering. Thin Solid Films, 2006, 503, 96-102.	1.8	11
85	Growth and characterization of well aligned densely packed IrO ₂ nanocrystals on sapphire via reactive sputtering. Journal of Physics Condensed Matter, 2006, 18, 1121-1136.	1.8	16
86	Modulation spectroscopy study of the effects of growth interruptions on the interfaces of GaAsSb/GaAs multiple quantum wells. Journal of Physics Condensed Matter, 2006, 18, 5927-5935.	1.8	6
87	Electrical Anisotropy of W-Doped ReSe ₂ Crystals. Journal of the Electrochemical Society, 2006, 153, J100.	2.9	12
88	Preparation and characterization of large niobium-doped MoSe ₂ single crystals. Journal of Crystal Growth, 2005, 285, 408-414.	1.5	40
89	The electrical and optical anisotropy of rhenium-doped WSe ₂ single crystals. Journal of Physics Condensed Matter, 2005, 17, 3575-3583.	1.8	24
90	The growth and characterization of well aligned RuO ₂ nanorods on sapphire substrates. Journal of Physics Condensed Matter, 2004, 16, 8475-8484.	1.8	38

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91	Temperature dependent photoreflectance and photoluminescence characterization of GaInNAs δ -GaAs single quantum well structures. Journal of Applied Physics, 2004, 96, 6298-6305.	2.5	15
92	Temperature dependences of energies and broadening parameters of the band-edge excitons of Re-doped WS ₂ and 2H-WS ₂ single crystals. Journal of Physics Condensed Matter, 2004, 16, 6995-7005.	1.8	19
93	Optical properties of GaSe $_{1-x}$ S $_x$ series layered semiconductors grown by vertical Bridgman method. Materials Chemistry and Physics, 2004, 88, 313-317.	4.0	44
94	Growth and characterization of OsO ₂ single crystals. Journal of Crystal Growth, 2004, 262, 271-276.	1.5	20
95	A comparative study of microstructure of RuO ₂ nanorods via Raman scattering and field emission scanning electron microscopy. Solid State Communications, 2004, 131, 349-353.	1.9	22
96	Field emission from vertically aligned conductive IrO ₂ nanorods. Applied Physics Letters, 2004, 84, 1552-1554.	3.3	75
97	The growth and characterization of rhenium-doped WS ₂ single crystals. Journal of Physics Condensed Matter, 2004, 16, 2171-2180.	1.8	24
98	Growth and characterization of tungsten and molybdenum-doped ReSe ₂ single crystals. Journal of Alloys and Compounds, 2004, 383, 63-68.	5.5	14
99	Growth and characterization of iridium dioxide nanorods. Journal of Alloys and Compounds, 2004, 383, 273-276.	5.5	25
100	Preparation and characterization of OsO ₂ . Journal of Alloys and Compounds, 2004, 383, 277-280.	5.5	7
101	Growth of IrO ₂ Films and Nanorods by Means of CVD: An Example of Compositional and Morphological Control of Nanostructures. Chemical Vapor Deposition, 2003, 9, 301-305.	1.3	35
102	Surface photovoltage spectroscopy as a valuable nondestructive characterization technique for GaAs/GaAlAs vertical-cavity surface-emitting laser structures. Journal of Physics Condensed Matter, 2003, 15, 55-66.	1.8	8
103	The first-order Raman spectra of OsO ₂ . Journal of Physics Condensed Matter, 2003, 15, 1487-1494.	1.8	4
104	Angle-dependent differential-photovoltage spectroscopy for the characterization of a GaAs/GaAlAs based vertical-cavity surface-emitting laser structure. Journal of Applied Physics, 2002, 92, 2350-2353.	2.5	6
105	Preparation and characterization of molybdenum-doped ReS ₂ single crystals. Journal of Physics Condensed Matter, 2002, 14, 4737-4746.	1.8	12
106	Temperature-dependent contactless electroreflectance and photoluminescence study of GaAlAs/InGaAs/GaAs pseudomorphic high electron mobility transistor structures. Journal of Applied Physics, 2001, 90, 6421-6427.	2.5	13
107	Novel electronic design for double-modulation spectroscopy of semiconductor and semiconductor microstructures. Review of Scientific Instruments, 2001, 72, 4218-4222.	1.3	1
108	Polarized electrolyte-electroreflectance study of ReS ₂ and ReSe ₂ layered semiconductors. Journal of Physics Condensed Matter, 2001, 13, 8145-8152.	1.8	13

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109	Polarized-photoreflectance characterization of an InGaP/InGaAsN/GaAsNpNdouble-heterojunction bipolar transistor structure. Journal of Applied Physics, 2001, 90, 4565-4569.	2.5	7
110	Surface photovoltage spectroscopy characterization of a GaAlAs/InGaAs/GaAs pseudomorphic high electron mobility transistor structure. Applied Physics Letters, 2001, 79, 949-951.	3.3	5
111	Room temperature polarized photoreflectance and photoluminescence characterization of AlGaAs/InGaAs/GaAs high electron mobility transistor structures. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 8, 297-305.	2.7	6
112	Temperature dependent polarized-piezoreflectance study of GaInP. Journal of Physics Condensed Matter, 2000, 12, 2183-2192.	1.8	3
113	In-plane anisotropy of the optical and electrical properties of layered ReS ₂ crystals. Journal of Physics Condensed Matter, 1999, 11, 5367-5375.	1.8	57
114	Temperature dependence of the band-edge exciton of a epilayer on GaAs. Semiconductor Science and Technology, 1999, 14, 85-88.	2.0	3
115	The electrical transport properties of ReS ₂ and ReSe ₂ layered crystals. Solid State Communications, 1999, 111, 635-640.	1.9	44
116	Crystal structure and band-edge transitions of ReS ₂ ^x Sex layered compounds. Journal of Physics and Chemistry of Solids, 1999, 60, 1797-1804.	4.0	69
117	Growth and characterization of rhenium-doped MoS ₂ single crystals. Journal of Crystal Growth, 1999, 205, 543-547.	1.5	53
118	Room-temperature phototransmittance and photoluminescence characterization of the AlGaAs/InGaAs/GaAs pseudomorphic high electron mobility transistor structures with varied quantum well compositional profiles. Semiconductor Science and Technology, 1999, 14, 103-109.	2.0	7
119	Temperature dependence of energies and broadening parameters of the band-edge excitons of single crystals. Journal of Physics Condensed Matter, 1998, 10, 9317-9328.	1.8	51
120	A second-harmonic electroreflectance study of a coupled GaAs - AlGaAs double quantum well. Semiconductor Science and Technology, 1997, 12, 1111-1115.	2.0	5
121	Piezoreflectance study of InP near the absorption edge. Semiconductor Science and Technology, 1996, 11, 1850-1856.	2.0	14
122	Anisotropy of Photoluminescence in Layered Semiconductors ReS ₂ and ReS ₂ :Au. Solid State Phenomena, 0, 170, 135-138.	0.3	13
123	Growth and Characterization of Well-Aligned RuO ₂ /R-TiO ₂ Heteronanostructures on Sapphire (100) Substrates by Reactive Magnetron Sputtering. Solid State Phenomena, 0, 170, 78-82.	0.3	0
124	Deposition and Characterization of Nanostructural IrO _x by RF Sputtering. Solid State Phenomena, 0, 194, 129-132.	0.3	3
125	Composition Dependent Band Gaps of Single Crystal Cu ₂ ZnSn(S _x Se _{1-x}) ₄ Solid Solutions. Solid State Phenomena, 0, 194, 139-143.		6
126	High-Temperature Optical Characterization of Transition Metal Dichalcogenides by Piezoreflectance Measurements. Solid State Phenomena, 0, 194, 158-161.	0.3	1